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Deposited by: Karen Cini-Mars

Karen Cini-Mars 8/7/03
(Signature & date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

On re application of _____: August 7, 2003
Deok-Kee Kim et al. _____: Group Art Unit:
Serial No. 10/604,384 _____: Examiner:
Filed: 07/16/2003 _____: International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: SIMPLIFIED TOP OXIDE LATE PROCESS

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

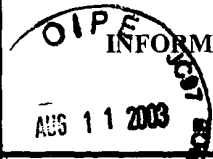
Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the prior patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

Respectfully submitted,
Kim et al.

By

Steven Capella
Steven Capella, Attorney
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 <p style="text-align: center;">INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p>	Docket Number (Optional) FIS920030088US1	Application Number 10/604,384
	Applicant(s) Deok-Kee Kim et al.	
	Filing Date 07/16/2003	Group Art Unit

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
		A Highly Cost Efficient 8F2 DRAM Cell with a Double Gate Vertical Transistor Device for 100 nm and Beyond, R. Weis et al., Infineon Technologies, IEDM 01-414, pp. 18.7.1-18.7.4, 3/01 IEEE

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.